

## UNITED STATES PATENT AND TRADEMARK OFFICE

UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Vignia 22313-1450 www.uspto.gov

## 

Rih Data Sheet

**CONFIRMATION NO. 5622** 

Junichi Sato, Tokyo, JAPAN; Setsuo Usui, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yoshifumi Mori, Chiba, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN;  ***CONTINUING DATA****  This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942  ***FOREIGN APPLICATIONS***  JAPAN P2000-269298 09/05/2000 JAPAN P2000-269298 09/05/2000 JAPAN P2000-2692961 09/05/2000 JAPAN P2000-269298 09/05/2000 JAPAN P2000-2692961 09/05/2000 JAPAN P2000-269298 09/05/2000 JAPAN P2000-2	BID Data Sneet										
Junichi Sato, Tokyo, JAPAN; Setsuo Usui, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yoshifumi Mori, Chiba, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN;  ***CONTINUING DATA****  This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942  ***FOREIGN APPLICATIONS***  JAPAN P2000-269298 09/05/2000 JAPAN P2000-269298 09/05/2000 JAPAN P2000-2692961 09/05/2000 JAPAN P2000-269298 09/05/2000 JAPAN P2000-2692961 09/05/2000 JAPAN P2000-269298 09/05/2000 JAPAN P2000-2			<b>DATE</b> 04/21/2004			GRO			DOCKET NO.		
Setsuo Usui, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yoshifumi Mori, Chiba, JAPAN; Hideharu Nakajima, Kanagawa, JAPAN;  ***CONTINUING DATA****  This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942  ***FOREIGN APPLICATIONS****  JAPAN P2000-2692898 09/05/2000 JAPAN P2000-269274 09/05/2000 JAPAN P2000-269261 09/05/2000 JAPAN P2000-269261 09/05/2000 JAPAN P2001-244163 08/10/2001  IF REQUIRED, FOREIGN FILING LICENSE GRANTED  ***09/02/2004  Foreign Priority claimed	APPLICANTS										
This application is a DIV of 09/946,898 09/05/2001 PAT 6,746,942  **FOREIGN APPLICATIONS************************************	Setsuo Usui, Kanagawa, JAPAN; Yasuhiro Sakamoto, Kanagawa, JAPAN; Yoshifumi Mori, Chiba, JAPAN;										
FILING FEE RECEIVED 770  FEES: Authority has been given in Paper RECEIVED 770  FILING FEE RECEIVED 770  FEES: Authority has been given in Paper RECEIVED 770  FEES: Authority has been given in Paper RECEIVED 770  FEES: Authority has been given in Paper No	** CONTINUING DATA **********************************										
FILING FEE RECEIVED 770  *** 09/02/2004  *** on o	** FOREIGN APPLICATIONS ************************************										
35 USC 119 (a-d) conditions yes no Met after Met Allowance Verified and Acknowledged Examiner's Signatule Ini)ials  ADDRESS 26263  TITLE  Semiconductor thin film and method of fabricating semiconductor thin film, apparatus for fabricating single crystal thin film, single crystal thin film substrate, and semiconductor device  FILING FEE RECEIVED 770  FEES: Authority has been given in Paper No to charge/credit DEPOSIT ACCOUNT No for following:    STATE OR COUNTRY DRAWING 22	** 09/02/2004										
TITLE  Semiconductor thin film and method of fabricating semiconductor thin film, apparatus for fabricating single crystal semiconductor thin film, and method of fabricating single crystal thin film, single crystal thin film substrate, and semiconductor device  FILING FEE RECEIVED 770  FEES: Authority has been given in Paper No to charge/credit DEPOSIT ACCOUNT No for following:    All Fees   1.16 Fees ( Filing )   1.17 Fees ( Processing Ext. of time )   1.18 Fees ( Issue )   1.18 Fees (	35 USC 119 (a-d) con	COUNTRY	DRA	DRAWING CLAI			_				
Semiconductor thin film and method of fabricating semiconductor thin film, apparatus for fabricating single crystal semiconductor thin film, and method of fabricating single crystal thin film, single crystal thin film substrate, and semiconductor device    FILING FEE   FEES: Authority has been given in Paper	ADDRESS 26263										
FILING FEE RECEIVED 770  FEES: Authority has been given in Paper No to charge/credit DEPOSIT ACCOUNT No for following:  1.16 Fees ( Filing )  1.17 Fees ( Processing Ext. of time )  1.18 Fees ( Issue )	TITLE  Semiconductor thin film and method of fabricating semiconductor thin film, apparatus for fabricating single crystal semiconductor thin film, and method of fabricating single crystal thin film, single crystal thin film substrate, and semiconductor device										
FILING FEE RECEIVED No to charge/credit DEPOSIT ACCOUNT No for following: 1.17 Fees ( Processing Ext. of time ) 1.18 Fees ( Issue ) Other							☐ All Fees				
RECEIVED No to charge/credit DEPOSIT ACCOUNT   time   1.18 Fees ( Issue )   Other	RECEIVED		·				☐ 1.16 Fees ( Filing )				
Other		No	to charge/cr	edit DEPOSIT ACCOUNT		NT	1.17 Fees ( Processing Ext. of time )				
		No	for following:				1.18 Fees ( Issue )				
							Oth	Other			
							☐ Credit				